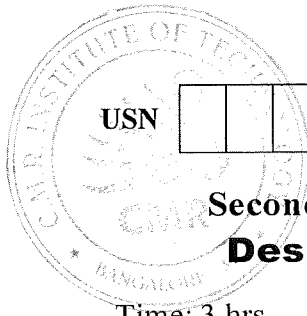


CBCS SCHEME



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18EVE21

Second Semester M.Tech. Degree Examination, June/July 2019 Design of Analog and Mixed Mode VLSI Circuits

Time: 3 hrs.

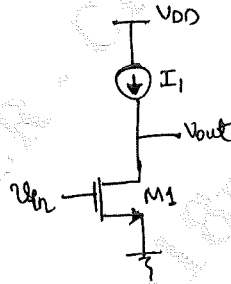
Max. Marks: 100

Note: Answer any FIVE full questions, choosing ONE full question from each module.

Module-1

- 1 a. Explain the small signal of a MOSFET including channel length modulation and body effect. Derive the expressions for output resistance ' r_o ' and trans conductance due to body effect ' g_{mb} '. (08 Marks)
- b. Derive the expression for voltage gain of a common source amplifier with resistive load by
i) Analytical method ii) Small signal model. (08 Marks)
- c. In Fig.Q.1(c), M_1 is in saturation. Give the expression for small signal voltage gain of the circuit. (04 Marks)

Fig.Q.1(c)



OR

- 2 a. Explain the second order effects that appear in MOSFET in detail. How these affect drain current? (10 Marks)
- b. Derive the expressions for voltage gain of a common source stage with source degeneration in presence of body effect and channel length modulation. (10 Marks)

Module-2

- 3 a. Derive the expression of small signal gain of source follower using
i) Analytical method ii) Small signal model. (10 Marks)
- b. Why non linearity is seen in source followers with NMOS? How this is eliminated? (04 Marks)
- c. For the circuit shown in Fig.Q.3(c)(i), $(W/L)_1 = 20/0.5$, $I_1 = 200\mu A$, $V_{TH0} = 0.6V$, $2\phi_F = 0.7V$, $\mu_n C_{Ox} = 50\mu A/V^2$ and $\gamma = 0.4V^{1/2}$
Calculate V_{out} for $V_{in} = 1.2V$
If I_1 is implemented as M_2 in Fig.Q.3(c)(ii), find the minimum value of $(W/L)_2$ for which M_2 remains saturated. (06 Marks)

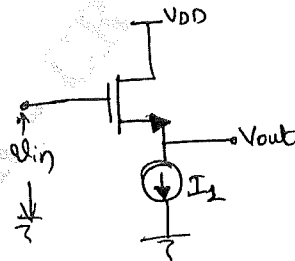


Fig.Q.3(c)(i)

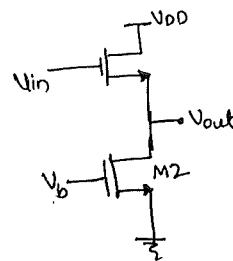


Fig.Q.3(c)(ii)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.
2. Any revealing of identification, appeal to evaluator and /or equations written eg. 42+8 = 50, will be treated as malpractice.

OR

- 4 a. Show that small signal gain of a common gate configuration is $A_v = g_m (1 + \eta)R_D$. (10 Marks)
 b. With relevant circuit diagram and equations, explain the working of 'Gilbert Cell'. Mention its merits and demerits. (10 Marks)

Module-3

- 5 a. Explain the basic current mirror with relevant equations. Also explain how the effect of channel length modulation is eliminated? (10 Marks)
 b. What are active current mirrors? Derive the expression for A_v for a differential pair with current source load along with equivalent circuit for calculation of G_m and R_{out} . (10 Marks)

OR

- 6 a. Explain the operation and advantages of a 2 stage op-amp with neat circuit diagram. (10 Marks)
 b. Compare single stage op-amp topology with 2 stage op-amp. (10 Marks)

Module-4

- 7 a. Explain slew rate and how do we optimize slew rate in op-amp design. (10 Marks)
 b. Calculate the low frequency PSRR of the feedback circuitry shown in Fig.Q.7(b). (10 Marks)

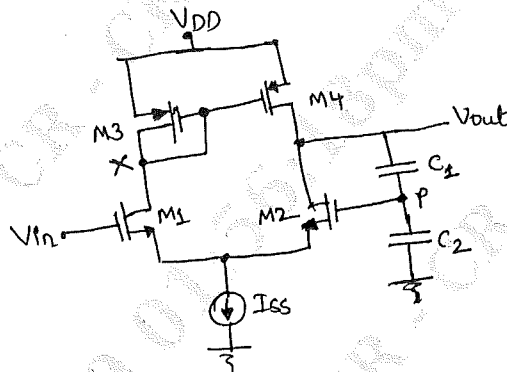


Fig.Q.7(b)

OR

- 8 a. Explain the operation of a simple charge pump PLL along with its dynamics. (10 Marks)
 b. Explain the different non-ideal effects in PLL. (10 Marks)

Module-5

- 9 a. Explain the operation of current steering DAC architecture with neat diagrams and equations. (10 Marks)
 b. Explain the operation of pipeline ADC architecture with neat diagrams and example. (10 Marks)

OR

- 10 a. Explain the operation of charge scaling DAC architecture and derive the expression for output voltage. (10 Marks)
 b. Explain the operation of successive approximation ADC with an architecture and example showing conversion steps. (10 Marks)
